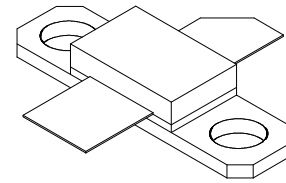


25W, 2.7 GHz, 28V Broadband RF Power N-Channel Enhancement-Mode Lateral MOSFET

Designed for base station applications in the frequency band 2.5 to 2.7 GHz. Rated with a minimum output power of 25W, it is ideal for CW and Multi-Tone Amplifiers in Class AB operation.

- ALL GOLD metal system for highest reliability
- Industry standard package
- Internally matched for repeatable manufacturing
- High gain, high efficiency and high linearity
- Integrated ESD Protection.
- Maximum gain and insertion phase flatness.
- Output load VSWR tolerance 10:1 all phase angles at 28V_{DC}, 2500MHz, 25W (CW) output power.
- Common source.



Package Type 440159

PN: UGF27025F

- **Application Specific Performance, 2.7 GHz**

- **Typical 2-Tone Performance**

- Average Load Power – 12.5 W

- η_D – 30%

- Power Gain – 11.5 dB

- IMD3: -30dBc @ -100kHz/ +100kHz

- VDD – 28V

- IDQ – 330mA

- **Typical CW Performance**

- Average Load Power – 25 W

- η_D – 38%

- Power Gain – 11.0 dB

- VDD – 28V

- IDQ – 330mA

Maximum Ratings

Rating	Symbol	Value	Unit
Drain to Source Voltage, Gate connected to Source	V_{DSS}	65	Volts
Gate to Source Voltage	V_{GSS}	+15 to -0.5	Volts
Total Device Dissipation @ Tcase = 70°C Derate above 70°C	P_D	83.5 0.48	Watts W/°C
Storage Temperature Range	T_{stg}	-65 to +150	°C
Maximum Operating Junction Temperature	T_J	200	°C

Thermal Characteristics

Characteristic	Symbol	Typical	Unit
Thermal Resistance, Junction to Case	Θ_{JC}	2.1	°C/W

Electrical DC Characteristics (Tc=25°C unless otherwise specified)

Rating	Symbol	Min	Typ	Max	Unit
Drain to Source Breakdown Voltage ($V_{GS}=0$, $I_D=1mA$)	BV_{DSS}	65	-	-	Volts
Drain to Source Leakage current ($V_{DS}=28V$, $V_{GS}=0$)	I_{DSS}	-	-	1.0	mA
Gate to Source Leakage current ($V_{GS}=15V$, $V_{DS}=0$)	I_{GSS}	-	-	1.0	μA
Threshold Voltage ($V_{DS}=10V$, $I_D=1mA$)	$V_{GS(th)}$	-	3.5	-	Volts
Gate Quiescent Voltage ($V_{DS}=28V$, $I_D=330mA$)	$V_{GS(Q)}$	3.0	4.0	5.0	Volts
Drain to Source On Voltage ($V_{GS}=10V$, $I_D=1A$)	$V_{DS(on)}$	-	-	0.33	Volts
Forward Transconductance ($V_{DS}=10V$, $I_D=1A$)	Gm	1.0	-	-	S

AC Characteristics (Tc=25°C unless otherwise specified)

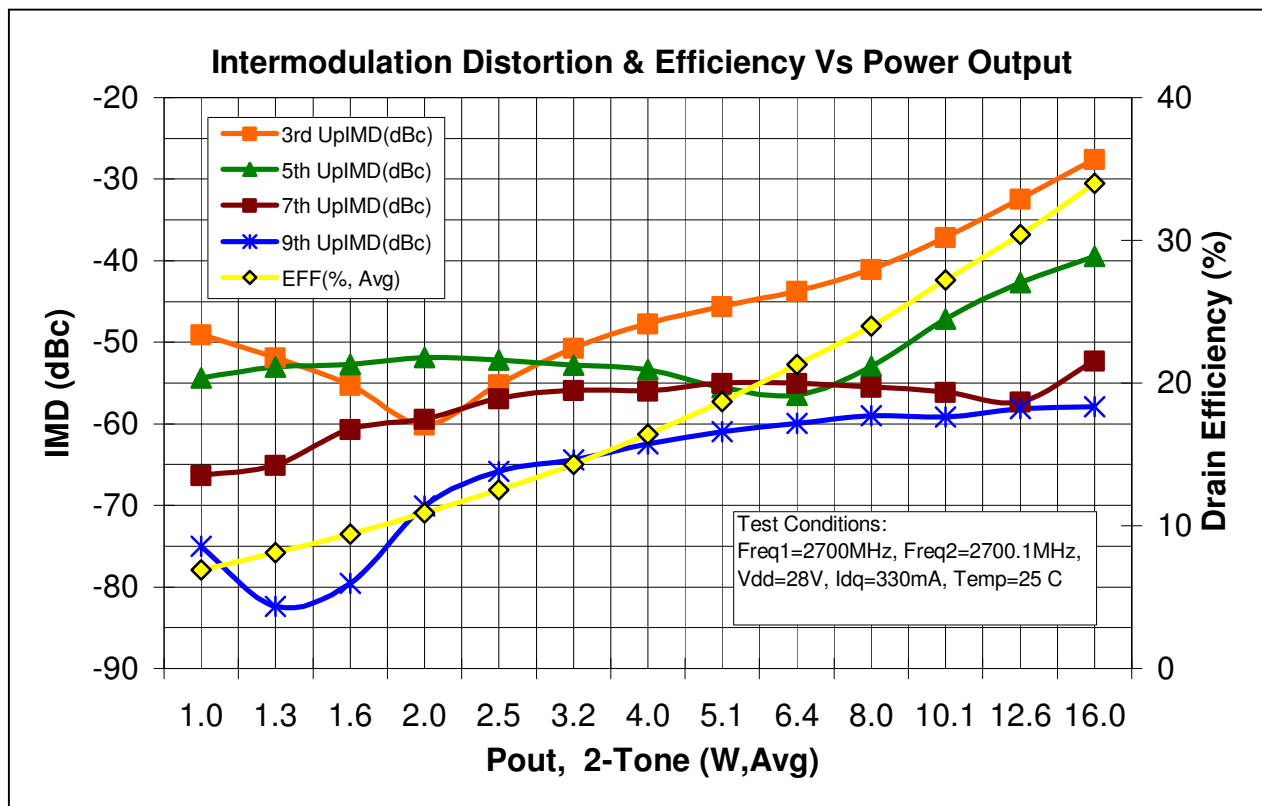
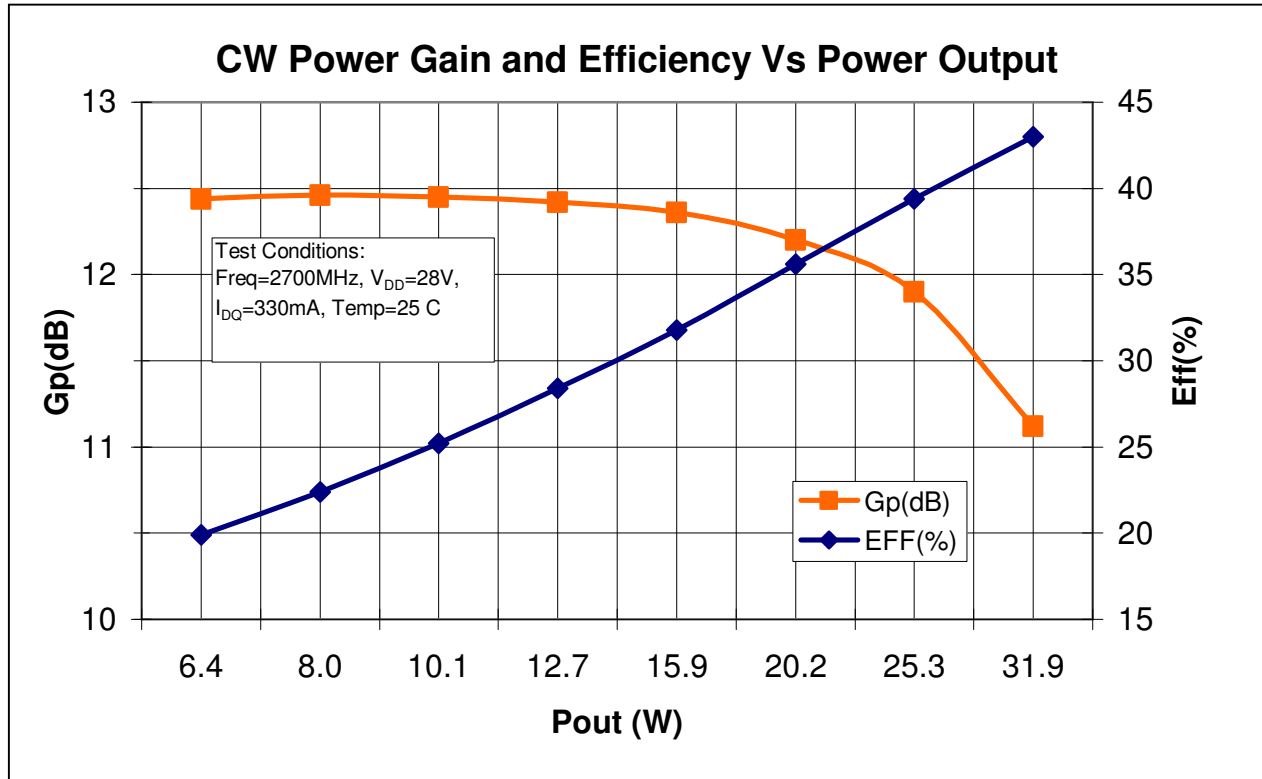
Rating	Symbol	Min	Typ	Max	Unit
Input capacitance * (including matching capacitor) (V _{DS} =28V, V _{GS} =0V, f = 1MHz)	C _{ISS}	-	74	-	pF
Output capacitance * (including matching capacitor) (V _{DS} = 28V, V _{GS} =0V, f = 1MHz)	C _{OSS}	-	352	-	pF
Feedback capacitance * (V _{DS} =28V, V _{GS} =0V, f = 1MHz)	C _{RSS}	-	1.6	-	pF

* Part is internally matched on input and output.

RF and Functional Tests (In Cree Microwave Broadband Fixture, Tc=25° C unless otherwise specified)

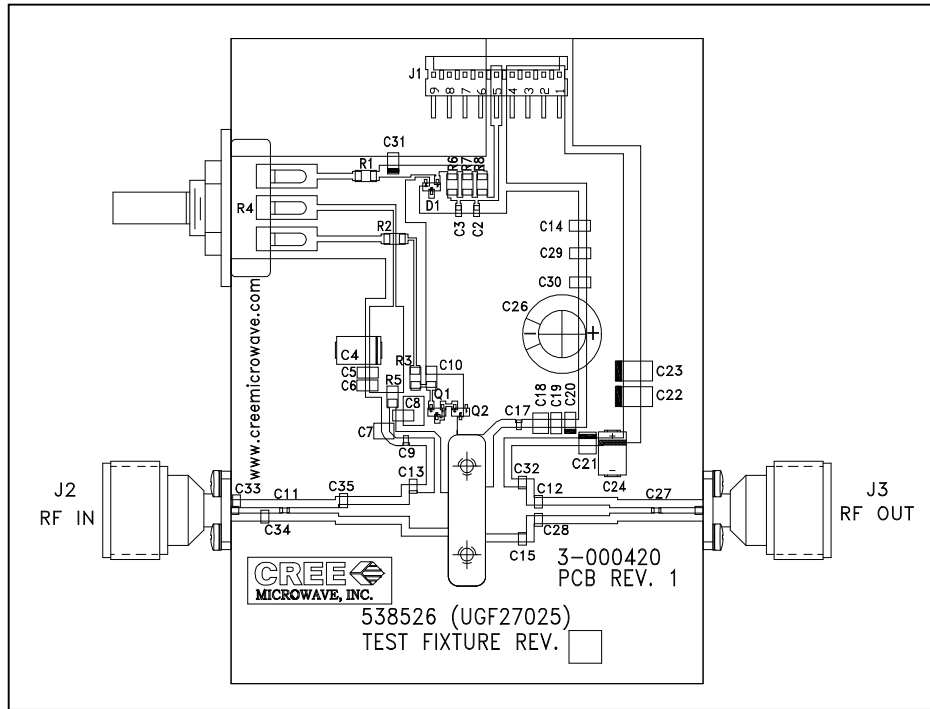
Rating	Symbol	Min	Typ	Max	Unit
CW Low Power Gain, P _{out} =8W V _{DD} =28V, I _{DQ} =330mA, f=2700 MHz	G _L	11	12	-	dB
CW Power Gain, P _{out} = 25 W V _{DD} =28V, I _{DQ} =330mA, f=2700 MHz	G _P	10	11	-	dB
CW Drain Efficiency, P _{out} = 25 W, f=2700 MHz, V _{DD} =28V, I _{DQ} =330mA	η _D	34	38	-	%
Two-Tone Common-Source Amplifier Power Gain V _{DD} =28V, I _{DQ} =330mA, P _{out} = 25 W PEP f ₁ =2700 MHz and f ₂ =2700.1 MHz	G _{TT}	10.5	11.5	-	dB
Two-Tone Intermodulation Distortion V _{DD} =28V, I _{DQ} =330mA, P _{out} = 25 W PEP f ₁ =2700 MHz and f ₂ =2700.1 MHz	I _{MD}	-	-30	-28	dBc
Two-Tone Drain Efficiency V _{DD} =28V, I _{DQ} =330mA, P _{out} = 25 W PEP f ₁ =2700 MHz and f ₂ =2700.1 MHz	η _{D2T}	26	30	-	%
Input Return Loss V _{DD} =28V, P _{out} = 25 W PEP, I _{DQ} =330mA f ₁ =2500 MHz and 2700 MHz, Tone Spacing = 100kHz	IRL	-	-	-9	dB
Load Mismatch Tolerance V _{DS} =28V, I _{DQ} = 330 mA, P _{out} =25W, f=2500 MHz	VSWR	10:1	-	-	Ψ

CAUTION - MOS Devices are susceptible to damage from Electrostatic Discharge (ESD). Appropriate precautions in handling, packaging and testing MOS devices must be observed.

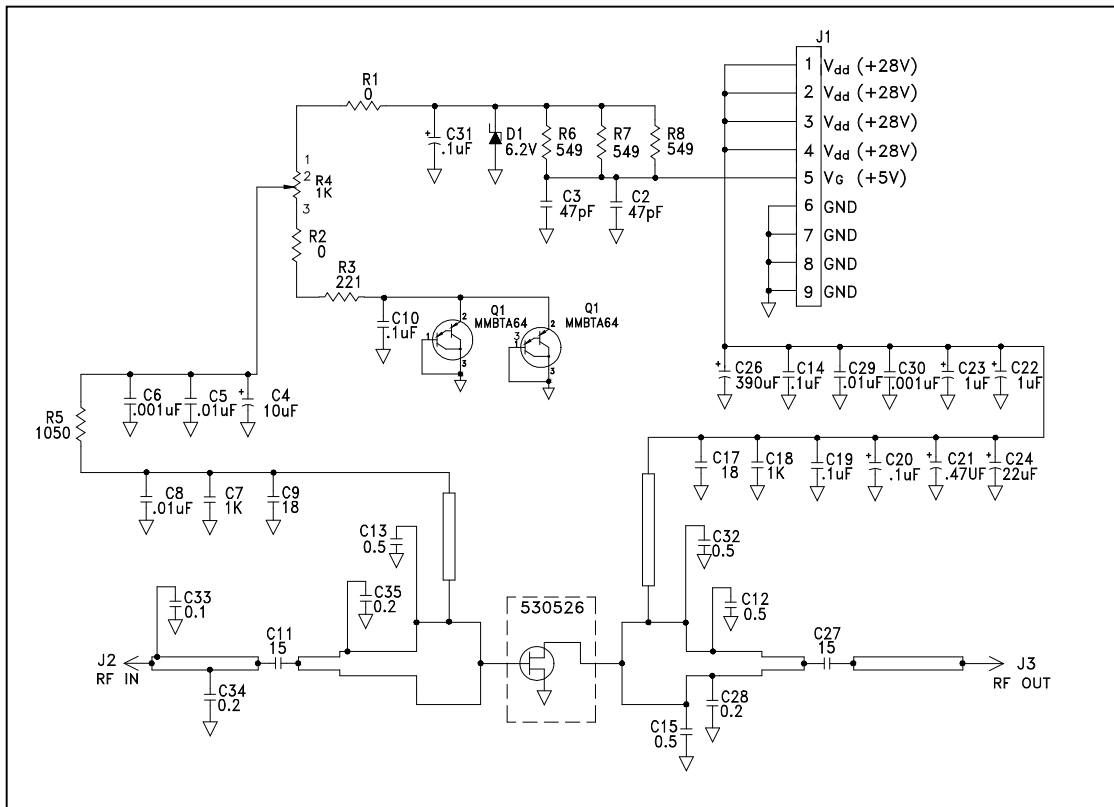


Test Fixture

Test Fixture Layout for 2.5-2.7GHz

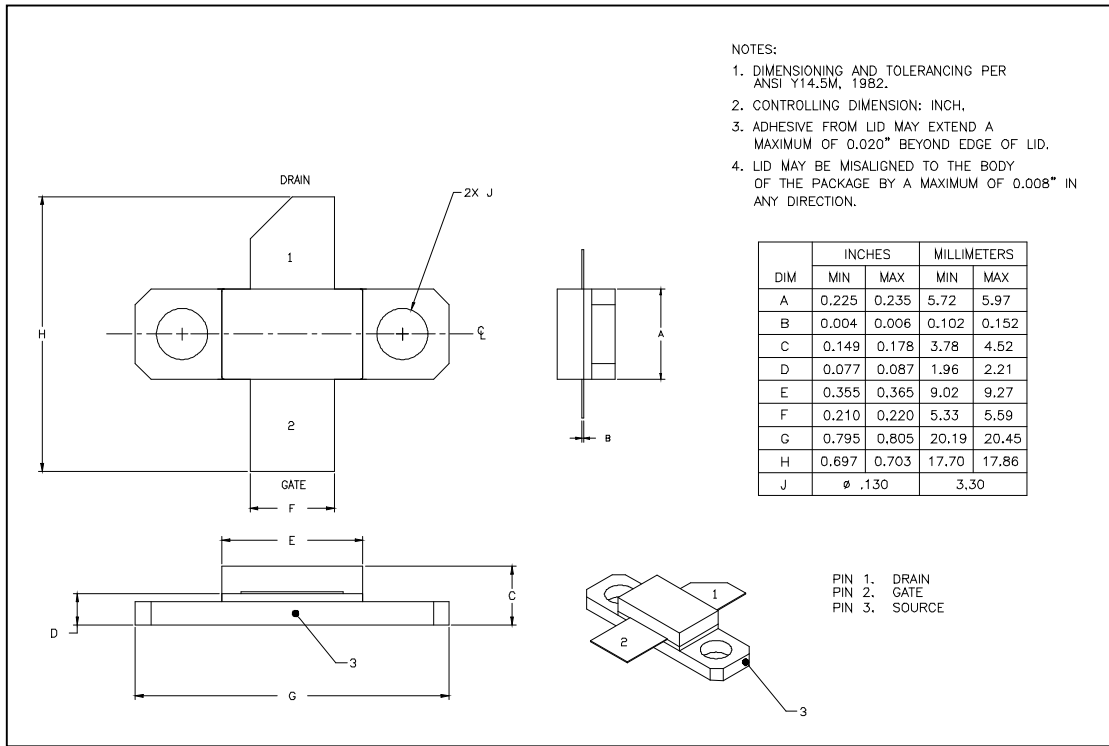


Test Fixture Schematic



Product Dimensions

UGF27025F -Package Number 440159





UGF27025

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